

### • General Description

The AGM215TS combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ .

This device is ideal for load switch and battery protection applications.

### • Features

- Advance high cell density Trench technology
- Low  $R_{DS(ON)}$  to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- 100% Avalanche tested
- 100% DVDS tested
- ESD

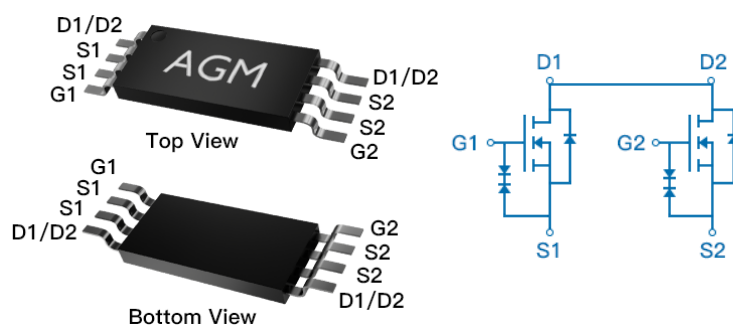
### • Application

- MB/VGA Vcore
- SMPS 2<sup>nd</sup> Synchronous Rectifier
- POL application
- BLDC Motor driver

### Product Summary

BVDSS	RDSON	ID
19.5V	11mΩ	7.0A

### TSSOP8 Pin Configuration



### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM215TS	AGM215TS	TSSOP8	330mm	12mm	3000

**Table 1. Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ )**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-Source Voltage ( $V_{GS}=0V$ )	19.5	V
$V_{GS}$	Gate-Source Voltage ( $V_{DS}=0V$ )	$\pm 10$	V
$I_D$	Drain Current-Continuous( $T_A=25^\circ\text{C}$ ) (Note 1)	7	A
	Drain Current-Continuous( $T_A=100^\circ\text{C}$ )	4.3	A
IDM (pulse)	Drain Current-Pulsed (Note 2)	28	A
$P_D$	Total Power Dissipation( $T_A=25^\circ\text{C}$ )	1.2	W
	Total Power Dissipation( $T_A=100^\circ\text{C}$ )	0.48	W
EAS	Avalanche energy (Note 3)	25	mJ
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ\text{C}$

**Table 2. Thermal Characteristic**

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient (Steady State) <sup>1</sup>	---	105	$^\circ\text{C/W}$

**Table 3. N- Channel Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

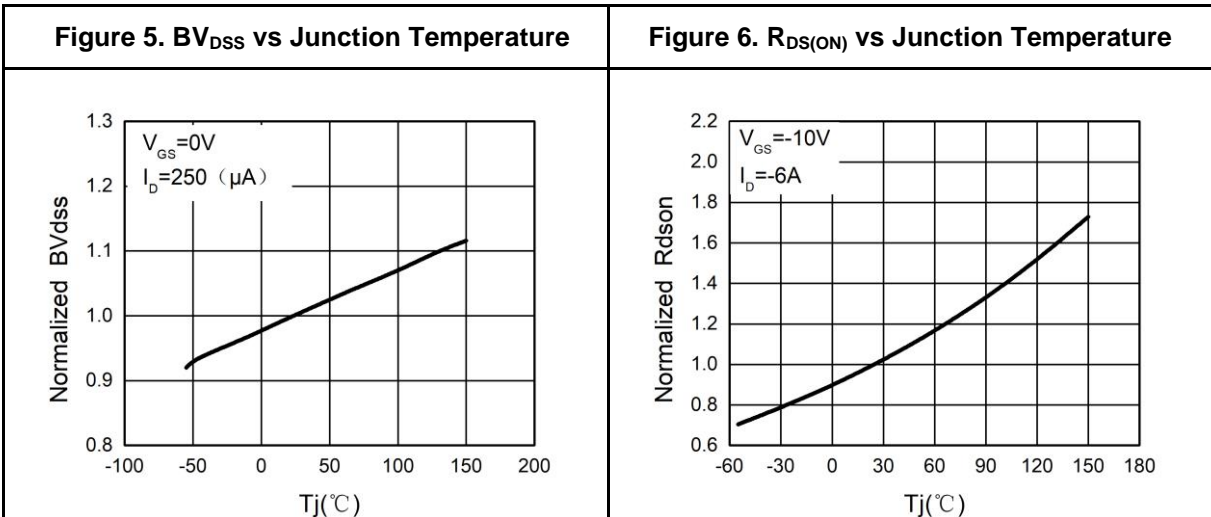
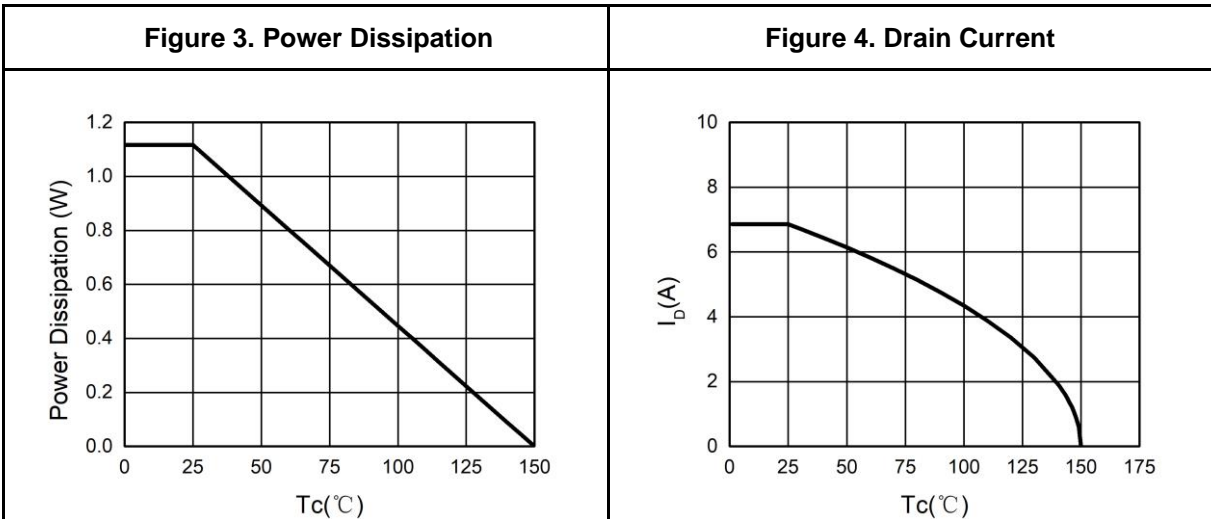
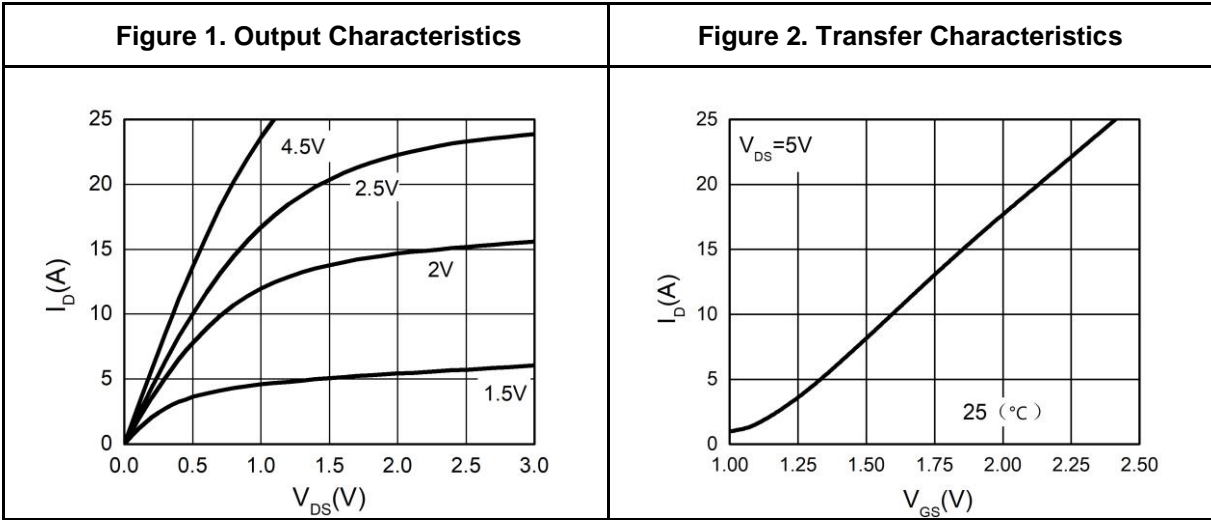
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>On/Off States</b>						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	19.5	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=18V,VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±10V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=250μA	0.5	0.7	1.0	V
gFS	Forward Transconductance	VDS=5V,ID=4A	--	13.6	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=4.5V, ID=5A	--	11	15	mΩ
		VGS=2.5V, ID=4A	--	14	19	mΩ
<b>Dynamic Characteristics</b>						
Ciss	Input Capacitance	VDS=10V,VGS=0V, F=1MHZ	--	854	--	pF
Coss	Output Capacitance		--	150	--	pF
Crss	Reverse Transfer Capacitance		--	90	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	--	--	Ω
<b>Switching Times</b>						
td(on)	Turn-on Delay Time	VGS=4.5V,VDS=10V RL=2Ω,RGEN=6Ω	--	11	--	nS
tr	Turn-on Rise Time		--	34	--	nS
td(off)	Turn-Off Delay Time		--	55	--	nS
tf	Turn-Off Fall Time		--	51	--	nS
Qg	Total Gate Charge	VGS=4.5V, VDS=10V, ID=5A	--	9.1	--	nC
Qgs	Gate-Source Charge		--	1.6	--	nC
Qgd	Gate-Drain Charge		--	2.0	--	nC
<b>Source-Drain Diode Characteristics</b>						
ISD	Source-Drain Current(Body Diode)		--	--	7.0	A
VSD	Forward on Voltage	VGS=0V,IS=5A	--	--	1.2	V
trr	Reverse Recovery Time	IF=5A , di/dt=100A/μs ,	--	--	--	ns
Qrr	Reverse Recovery Charge	TJ=25°C	--	--	--	nc

Notes 1.The maximum current rating is package limited.

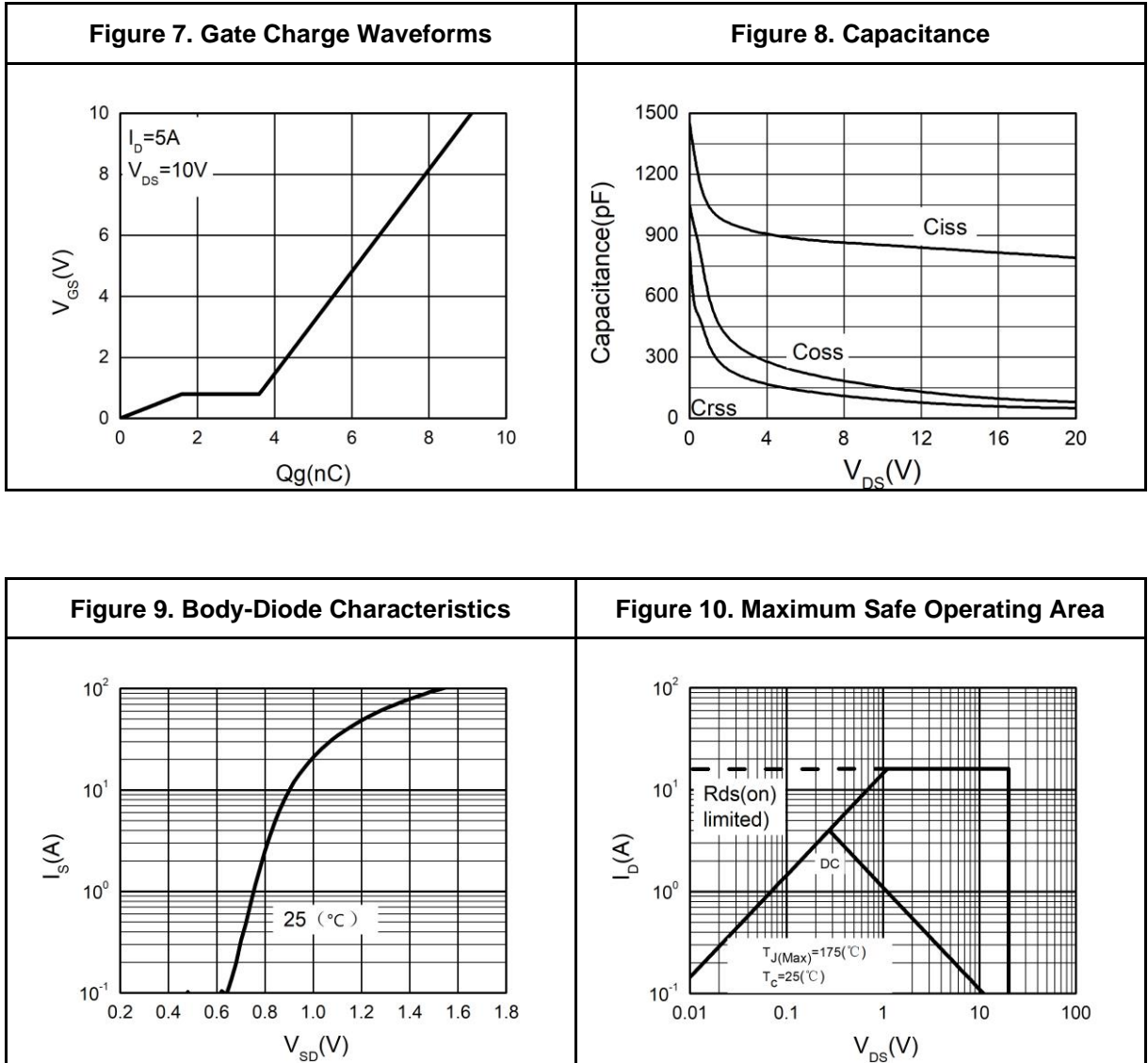
Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: T<sub>J</sub>=25°C

### Typical Electrical And Thermal Characteristics (Curves)

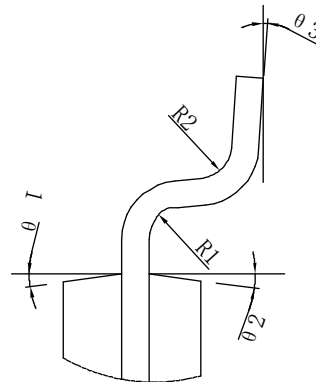
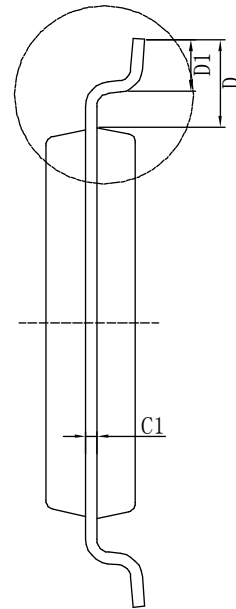
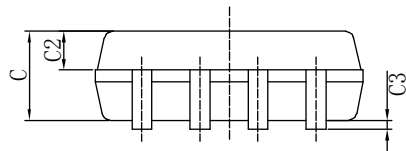
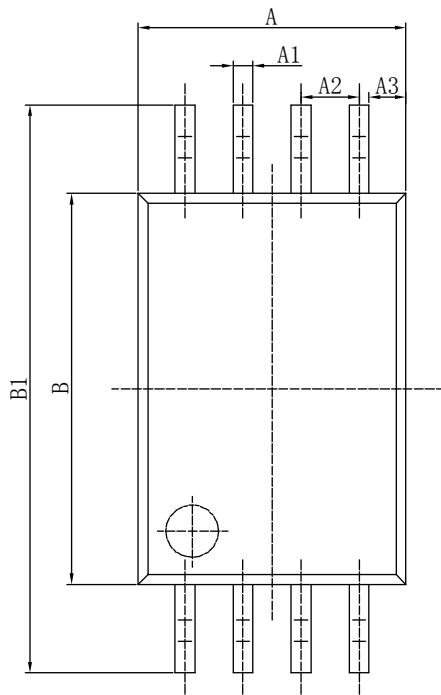


### Typical Electrical And Thermal Characteristics (Curves)



**Package Mechanical Data TSSOP8**

标注	尺寸	最小(mm)	最大(mm)	标注	尺寸	最小(mm)	最大(mm)
A		2.90	3.10	C3		0.05	0.15
A1		0.20	0.30	D		1.00REF	
A2		0.65 TYP		D1		0.50	0.70
A3		0.36	0.46	R1		0.15TYP	
B		4.30	4.50	R2		0.15TYP	
B1		6.30	6.50	$\theta 1$		12° TYP4	
C		0.95	1.05	$\theta 2$		12° TYP4	
C1		0.127 TYP		$\theta 3$		0° ~ 7°	
C2		0.39	0.49				




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